



ZXMP6A17E6Q

Product Summary

V _{(BR)DSS}	R _{DS(on)} Max	I _D Max T _A = +25°C (Note 7)	
60)/	$125m\Omega @ V_{GS} = -10V$	-3.0 A	
-60V	190mΩ @ V_{GS} = -4.5V	-2.4 A	

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Disconnect switches
- Motor control

60V P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

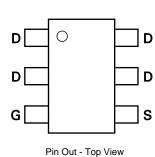
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low input capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available

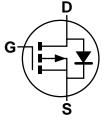
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over sopper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (approximate)



Top View





Equivalent Circuit

Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Quantity per reel
	Compliance	Case	Qualitity per reer
ZXMP6A17E6QTA	Automotive	SOT26	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

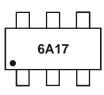
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Note:



6A17 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source voltage		V _{DSS}	-60	V	
Gate-Source voltage		V _{GS}	±20	V	
		(Note 7)		-3.0	
Continuous Drain current	$V_{GS} = 10V$	$T_A = +70^{\circ}C$ (Note 7)	I _D	-2.4	А
		(Note 6)		-2.3	
Pulsed Drain current	$V_{GS} = 10V$	(Note 8)	IDM	-13.6	А
Continuous Source current (Body diode)	(Note 7)	I _S	-2.5	А
Pulsed Source current (Body diode) (Note 8)		I _{SM}	-13.6	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power dissipation	(Note 6)		1.1 8.8	W mW/°C	
Linear derating factor	(Note 7)	PD PD	1.92 15.4		
Thermal Desistance Junction to Ambient	(Note 6)	P	113	00404	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	65	°C/W	
Operating and storage temperature range		TJ, T _{STG}	-55 to +150	°C	

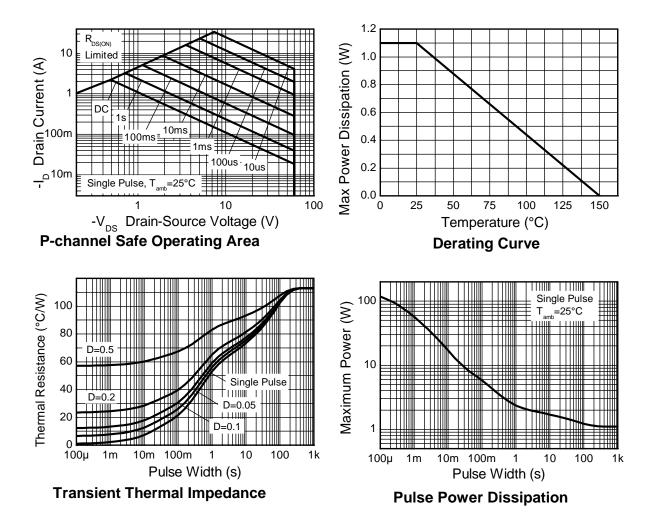
Notes: 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

7. Same as note (6), except the device is measured at t \leq 5 sec.

8. Same as note (6), except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.



Thermal Characteristics





Notes:

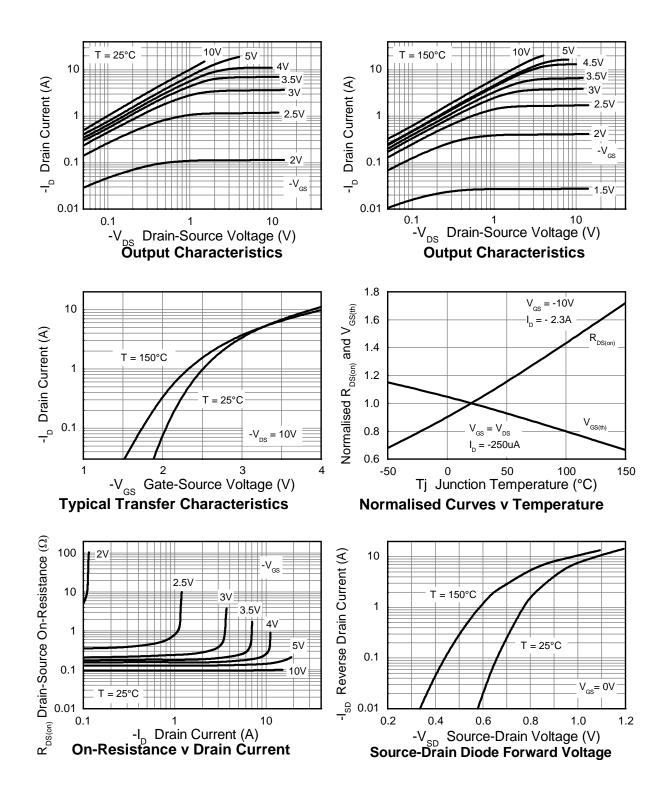
Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test C	Condition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1.0	μΑ	$V_{DS} = -60V, V_{GS}$	s = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20 V, V_D$	s = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	-3.0	V	$I_{D} = -250 \mu A, V_{D}$	s = V _{GS}
Statia Drain Source On Desistance (Note 0)			0.100	0.125	Ω	$V_{GS} = -10V, I_{D} =$	= -2.3A
Static Drain-Source On-Resistance (Note 9)	R _{DS (ON)}		0.130	0.190	Ω	$V_{GS} = -4.5V, I_{D}$	= -1.9A
Forward Transconductance (Notes 9 & 10)	g fs	_	4.7		S	V _{DS} = -15V, I _D = -2.3A	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	$I_{S} = -2.0A, V_{GS} = 0V$	
Reverse recovery time (Note 10)	t _{rr}		25.1		ns	I _F = -1.7A, di/dt = 100A/μs	
Reverse recovery charge (Note 10)	Q _{rr}	_	27.2		nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		637	_	pF	V _{DS} = -30V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	70		pF		
Reverse Transfer Capacitance	C _{rss}	_	53		pF		
Total Gate Charge (Note 11)	Qq		9.8		nC	$V_{GS} = -5.0V$	
Total Gate Charge (Note 11)	Qg		17.7		nC	$V_{GS} = -10V$ $V_{DS} = -30V$ $V_{DS} = -2.3A$	
Gate-Source Charge (Note 11)	Q _{gs}		1.6		nC		
Gate-Drain Charge (Note 11)	Q _{qd}		4.4		nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.6		ns	$V_{DD} = -30V, V_{GS} = -10V$ $I_D = -1.0A, R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 11)	tr		3.4		ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	26.2		ns		
Turn-Off Fall Time (Note 11)	t _f		11.3		ns		

9. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
10. For design aid only, not subject to production testing.
11. Switching characteristics are independent of operating junction temperatures.

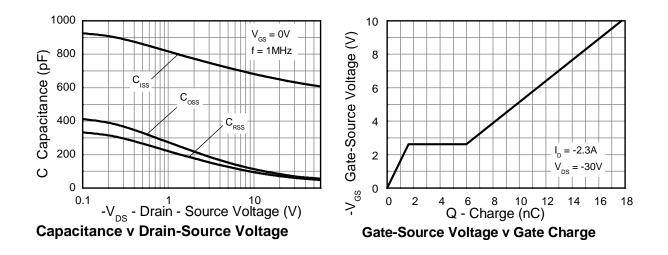


Typical Characteristics

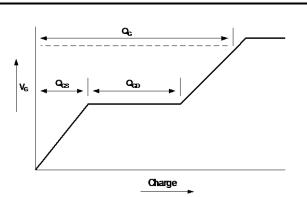




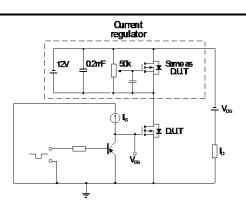
Typical Characteristics (cont.)



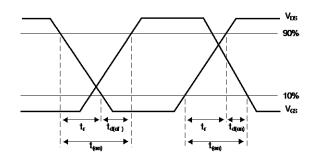
Test Circuits



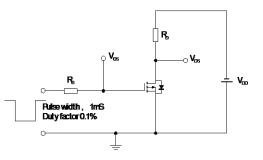
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

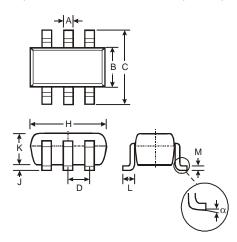


Switching time test circuit



Package Outline Dimensions

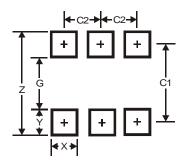
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D			0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
κ	1.00 1.30 1		1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
α	α 0° 8° —				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
Z	3.20		
G	1.60		
Х	0.55		
Y	0.80		
C1	2.40		
C2	0.95		



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